

PLUS Search Results for S/N 10/643,718, Searched January 23, 2004 (Top 50)

5212397	5719081	5498554	5433168	4411060
5279978	5866468	5501994	5604150	4559638
5731619	5892256	5747850	5612230	4616242
5789286	6002158	6072217	5914245	4621276
6005285	6180985	5315144	5940324	4633030
6204153	6194253	5501993	5942781	4893164
4914491	6239469	5814866	5994162	5250835
5250460	6335542	6100567	6137142	5258322
4499558	6344116	5010385	6140161	5372958
5612246	4584027	5395773	6188136	5399514

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/643,718 on January 23, 2004

Combined Classifications

9 257/E27.112
8 257/347
6 257/E27.064
5 257/E21.644
5 438/228
4 257/351
4 257/E21.544
4 438/527
3 257/349
3 257/350
3 257/369
3 257/371
3 257/372
3 257/66
3 257/E21.215
3 257/E21.435
3 257/E21.567
3 257/E27.06
3 257/E27.067
3 257/E29.061
3 257/E29.062
3 438/200
3 438/231
3 438/479
3 438/526
2 148/DIG 150
2 257/344
2 257/354
2 257/365
2 257/376
2 257/377
2 257/392
2 257/408
2 257/E21.106
2 257/E21.413
2 257/E21.415
2 257/E21.443
2 257/E21.564
2 257/E21.633
2 257/E21.703
2 257/E27.015
2 257/E29.055
2 257/E29.086
2 257/E29.107
2 257/E29.281
2 438/149
2 438/154
2 438/290
2 438/406
2 438/481

10643718_CLS

2 438/517
2 438/529
2 438/928

10643718_CLSTITLES

Titles of Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/643,718 on January 23, 2004

8 257/347 (3 OR, 5 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
- 257/347 ..Single crystal semiconductor layer on insulating substrate (SOI)

6 257/E27.064 (0 OR, 6 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/E27.006 .Including piezo-electric, electro-resistive, or magneto-resistive component (EPO)
- 257/E27.009 .Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Including integrated passive circuit elements (EPO)
- 257/E27.01 ..With semiconductor substrate only (EPO)
- 257/E27.046 ...Including only semiconductor components of a single kind, e.g., all bipolar transistors, all diodes, or all CMOS (EPO)
- 257/E27.059Including field-effect component only (EPO)
- 257/E27.06Field-effect transistor with insulated gate (EPO)
- 257/E27.062Complementary MIS (EPO)
- 257/E27.064Combination of complementary transistors having a different structure, e.g. stacked CMOS, high-voltage and low-voltage CMOS (EPO)

5 438/228 (1 OR, 4 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

- 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
- 438/197 .Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.)
- 438/199 ..Complementary insulated gate field effect transistors (i.e., CMOS)
- 438/218 ...Including isolation structure
- 438/225Recessed oxide formed by localized oxidation (i.e., LOCOS)
- 438/227Having well structure of opposite conductivity type
- 438/228Plural wells

4 257/351 (2 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity

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- channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
- 257/347 ..Single crystal semiconductor layer on insulating substrate (SOI)
- 257/350 ...Insulated electrode device is combined with diverse type device (e.g., complementary MOSFETs, FET with resistor, etc.)
- 257/351Complementary field effect transistor structures only (i.e., not including bipolar transistors, resistors, or other components)
- 4 438/527 (1 OR, 3 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/510 INTRODUCTION OF CONDUCTIVITY MODIFYING DOPANT INTO SEMICONDUCTIVE MATERIAL
- 438/514 .Ion implantation of dopant into semiconductor region
- 438/527 ..Including multiple implantation steps